Takashi Kita

List of Publications by Year in Descending Order

223 papers	3,033 citations	28 h-index	46 g-index
272 ext. papers	3,418 ext. citations	2.6 avg, IF	4.93 L-index

#	Paper	IF	Citations
223	Yb-doped YAlO thin films with a self-organized columnar structure and their anti-Stokes photoluminescence properties. *AIP Advances*, **2022**, 12, 025110	1.5	
222	Modulation of exciton states through resonant excitation by continuous wave lasers in a GaAs/AlAs multiple quantum well. *Journal Physics D: Applied Physics*, **2021**, 54, 335106	3	0
221	Two-step excitation induced photovoltaic properties in an InAs quantum dot-in-well intermediate-band solar cell. *Journal of Applied Physics*, **2021**, 129, 074503	2.5	2
220	Increase in terahertz-wave generation by difference frequency mixing by the overlap of exciton states in different GaAs/AlAs quantum wells and spectroscopic measurements. *Optics Express*, **2021**, 29, 24387-24395	3.3	1
219	Voltage boost effects in two-step photon upconversion solar cells with a modulation-doped structure. *Journal of Applied Physics*, **2021**, 130, 085701	2.5	1
218	Two-photon photocurrent spectra of InAs quantum dot-in-well intermediated-band solar cells at room temperature. *Journal of Applied Physics*, **2021**, 130, 124505	2.5	0
217	Determination of silicon wafer site flatness using dual heterodyne interferometers with sub-nanometer precision. *Review of Scientific Instruments*, **2020**, 91, 065114	1.7	0
216	Polarization-insensitive fiber-to-fiber gain of semiconductor optical amplifier using closely stacked InAs/GaAs quantum dots. *Japanese Journal of Applied Physics*, **2020**, 59, 032002	1.4	3
215	Properties of Anti-Stokes Photoluminescence and Ideal Laser Cooling Performance in Yb-Doped Yttrium Aluminum Garnet Thin Film. *Zairyo/Journal of the Society of Materials Science, Japan*, **2020**, 69, 727-732	0.1	1
214	An energy transfer accompanied by phonon absorption in ytterbium-doped yttrium aluminum perovskite for optical refrigeration. *Applied Physics Letters*, **2020**, 117, 041104	3.4	2
213	Infrared photodetector sensitized by InAs quantum dots embedded near an AlGaAs/GaAs heterointerface. *Scientific Reports*, **2020**, 10, 11628	4.9	12
212	Electron transport in a silicon crystal observed by energy transfer luminescence. *Japanese Journal of Applied Physics*, **2020**, 59, 082005	1.4	0
211	Reciprocal Relation Between Intraband Carrier Generation and Interband Recombination at the Heterointerface of Two-Step Photon Up-Conversion Solar Cells. *Physical Review Applied*, **2020**, 14,	4.3	2
210	Resonant exciton excitation photoluminescence and dynamics in a GaAs/AlAs multiple quantum well with internal electric field. *AIP Advances*, **2020**, 10, 095016	1.5	3
209	Adiabatic two-step photoexcitation effects in intermediate-band solar cells with quantum dot-in-well structure. *Scientific Reports*, **2019**, 9, 7859	4.9	4
208	Reply to: "Thermal artefacts in two-photon solar cell experiments". *Nature Communications*, **2019**, 10, 956	17.4	5
207	Wide-wavelength-range control of photoluminescence polarization in closely stacked InAs/GaAs quantum dots. *Journal of Applied Physics*, **2019**, 125, 234304	2.5	5

206	Exciton dynamics as a function of excitation intensity and double-pulse excitation in cyanine molecule thin films: Toward low-power optical switches. *Journal of Applied Physics*, **2019**, 126, 033103	2.5	
205	Actual Calculation of Solar Cell Efficiencies. *Green Energy and Technology*, **2019**, 81-137	0.6	
204	Hot-carrier generation and extraction in InAs/GaAs quantum dot superlattice solar cells. *Semiconductor Science and Technology*, **2019**, 34, 094003	1.8	7
203	Energy Conversion Efficiency of Solar Cells. *Green Energy and Technology*, **2019**,	0.6	5
202	Ideal Laser Cooling Efficiency Utilizing Anti-Stokes Luminescence in Yb-Doped Yttrium Aluminum Garnet Powder Crystals. *Zairyo/Journal of the Society of Materials Science, Japan*, **2019**, 68, 762-766	0.1	
201	Improving laser cooling efficiencies of Yb-doped yttrium aluminum garnet by utilizing non-resonant anti-Stokes emission at high temperatures. *Optics Express*, **2019**, 27, 34961-34973	3.3	5
200	Effects of a thin nitrogen-doped layer on terahertz dynamics in GaAs containing InAs quantum dots. *OSA Continuum*, **2019**, 2, 1621	1.4	
199	Optical Response of Two-Dimensional Photonic Crystal on Metal. *Zairyo/Journal of the Society of Materials Science, Japan*, **2019**, 68, 757-761	0.1	
198	Bound-to-continuum intraband transition properties in InAs/GaAs quantum dot superlattice solar cells. *Applied Physics Express*, **2019**, 12, 125008	2.4	2
197	Increasing conversion efficiency of two-step photon up-conversion solar cell with a voltage booster hetero-interface. *Scientific Reports*, **2018**, 8, 872	4.9	8
196	Two-step photocurrent generation enhanced by the fundamental-state miniband formation in intermediate-band solar cells using a highly homogeneous InAs/GaAs quantum-dot superlattice. *Applied Physics Express*, **2018**, 11, 012301	2.4	3
195	Effect of lattice-mismatch strain on electron dynamics in InAs/GaAs quantum dots as seen by time-domain terahertz spectroscopy. *Journal Physics D: Applied Physics*, **2018**, 51, 305102	3	3
194	Hot-carrier generation in a solar cell containing InAs/GaAs quantum-dot superlattices as a light absorber. *Applied Physics Express*, **2018**, 11, 082303	2.4	3
193	Wide Frequency Tuning of Continuous Terahertz Wave Generated by Difference Frequency Mixing under Exciton-Excitation Conditions in a GaAs/AlAs Multiple Quantum Well. *Physical Review Applied* , **2018**, 10,	4.3	4
192	Effects of non-exciton components excited by broadband pulses on quantum beats in a GaAs/AlAs multiple quantum well. *Scientific Reports*, **2017**, 7, 41496	4.9	3
191	Two-step photocurrent generation enhanced by miniband formation in InAs/GaAs quantum dot superlattice intermediate-band solar cells. *Applied Physics Letters*, **2017**, 110, 193104	3.4	7
190	Two-step photon up-conversion solar cells. *Nature Communications*, **2017**, 8, 14962	17.4	66
189	Ferromagnetic resonance features of degenerate GdN semiconductor. *Physics Letters, Section A: General, Atomic and Solid State Physics*, **2017**, 381, 1905-1909	2.3	1

188	Excitation of Thin Cyanine Films via Energy Transfer from Si Substrate. *Journal of the Physical Society of Japan*, **2017**, 86, 094710	1.5	1
187	Recent Advancement of Semiconductor Materials and Devices. *Zairyo/Journal of the Society of Materials Science, Japan*, **2017**, 66, 244-249	0.1	
186	Fundamental Device Characteristics of Hot Carrier Solar Cell Using InAs/GaAs Quantum Dot Superlattices.. *Zairyo/Journal of the Society of Materials Science, Japan*, **2017**, 66, 629-633	0.1	
185	Efficient two-step photocarrier generation in bias-controlled InAs/GaAs quantum dot superlattice intermediate-band solar cells. *Scientific Reports*, **2017**, 7, 5865	4.9	14
184	Spatially resolved electronic structure of an isovalent nitrogen center in GaAs. *Physical Review B*, **2017**, 96,	3.3	6
183	Effects of exciton line widths on the amplitude of quantum beat oscillations. *Applied Physics Express*, **2016**, 9, 062801	2.4	2
182	Nanosecond-scale hot-carrier cooling dynamics in one-dimensional quantum dot superlattices. *Physical Review B*, **2016**, 93,	3.3	16
181	Organic-Lead Halide Perovskite Solar Cell with ITO Transparent Electrode Deposited by Sputtering Process. *Zairyo/Journal of the Society of Materials Science, Japan*, **2016**, 65, 642-646	0.1	
180	Saturable Two-Step Photocurrent Generation in Intermediate-Band Solar Cells Including InAs Quantum Dots Embedded in Al$_{0.3}$Ga$_{0.7}$ As/GaAs Quantum Wells. *IEEE Journal of Photovoltaics*, **2016**, 6, 465-472	3.7	18
179	Increase in exciton decay rate due to plane-to-plane interaction between cyanine thin films. *AIP Advances*, **2016**, 6, 075209	1.5	3
178	Polarization characteristics of electroluminescence and net modal gain in highly stacked InAs/GaAs quantum-dot laser devices. *Journal of Applied Physics*, **2016**, 120, 134313	2.5	3
177	Effects of rapid thermal annealing on two-dimensional delocalized electronic states of the epitaxial N-doped layer in GaAs. *Applied Physics Letters*, **2016**, 108, 111905	3.4	4
176	Photocarrier transport dynamics in InAs/GaAs quantum dot superlattice solar cells using time-of-flight spectroscopy. *Physical Review B*, **2016**, 94,	3.3	6
175	Emission-wavelength tuning of InAs quantum dots grown on nitrogen-doped GaAs(001). *Journal of Applied Physics*, **2016**, 119, 194306	2.5	4
174	Effective drift mobility approximation in multiple quantum-well solar cell **2016**,		3
173	Fabrication of cyanine dye thin films grown by a layer-by-layer method. *Materials Research Express*, **2015**, 2, 076402	1.7	4
172	Intermediate band solar cells: Recent progress and future directions. *Applied Physics Reviews*, **2015**, 2, 021302	17.3	222
171	Microscopic properties of degradation-free capped GdN thin films studied by electron spin resonance. *Journal of Applied Physics*, **2015**, 117, 043909	2.5	3

170	Thermal annealing effects on ultra-violet luminescence properties of Gd doped AlN. *Journal of Applied Physics*, **2015**, 117, 163105	2.5	8
169	. *IEEE Journal of Photovoltaics*, **2015**, 5, 1613-1620	3.7	9
168	Rapid dephasing related to intersubband transitions induced by exciton quantum beats observed by a pump-probe technique in a GaAs/AlAs multiple quantum well. *Physical Review B*, **2015**, 91,	3.3	3
167	Two-step photon absorption in InAs/GaAs quantum-dot superlattice solar cells. *Physical Review B*, **2015**, 91,	3.3	29
166	Broadband control of emission wavelength of InAs/GaAs quantum dots by GaAs capping temperature. *Journal of Applied Physics*, **2015**, 118, 154301	2.5	15
165	Microscopic observation of carrier-transport dynamics in quantum-structure solar cells using a time-of-flight technique. *Applied Physics Letters*, **2015**, 107, 043901	3.4	11
164	Analysis of Optical Waveguide Mode in Closely-Stacked InAs/GaAs Quantum Dot Semiconductor Optical Amplifiers. *Zairyo/Journal of the Society of Materials Science, Japan*, **2015**, 64, 685-689	0.1	
163	Effect of exciton oscillator strength on upconversion photoluminescence in GaAs/AlAs multiple quantum wells. *Applied Physics Letters*, **2014**, 105, 181901	3.4	7
162	Epitaxial two-dimensional nitrogen atomic sheet in GaAs. *Applied Physics Letters*, **2014**, 104, 041907	3.4	14
161	Suppression of thermal carrier escape and efficient photo-carrier generation by two-step photon absorption in InAs quantum dot intermediate-band solar cells using a dot-in-well structure. *Journal of Applied Physics*, **2014**, 116, 063510	2.5	23
160	Pulse modulation towards low-power operation based on the quantum beat of excitons in a GaAs/AlAs multiple quantum well. *Journal Physics D: Applied Physics*, **2014**, 47, 105101	3	4
159	Polarization-insensitive optical gain characteristics of highly stacked InAs/GaAs quantum dots. *Journal of Applied Physics*, **2014**, 115, 233512	2.5	14
158	Control of optical properties in cyanine dye thin film fabricated by a layer-by-layer method. *Journal of Applied Physics*, **2014**, 115, 083503	2.5	6
157	Electronic transitions in GdN band structure. *Journal of Applied Physics*, **2014**, 115, 203717	2.5	5
156	Resonant indirect excitation of Gd3+ in AlN thin films. *Journal of Applied Physics*, **2014**, 115, 173508	2.5	1
155	Effect of internal electric field on InAs/GaAs quantum dot solar cells. *Journal of Applied Physics*, **2014**, 115, 083510	2.5	27
154	Hot-carrier solar cells using low-dimensional quantum structures. *Applied Physics Letters*, **2014**, 105, 171904	3.4	14
153	Carrier Time-of-Flight Measurement Using a Probe Structure for Direct Evaluation of Carrier Transport in Multiple Quantum Well Solar Cells. *IEEE Journal of Photovoltaics*, **2014**, 4, 1518-1525	3.7	8

152	Tuning optical and ferromagnetic properties of thin GdN films by nitrogen-vacancy centers. *European Physical Journal B*, **2013**, 86, 1	1.2	9
151	Polarization controlled emisson from closely stacked InAs/GaAs quantum dots. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2013**, 10, 1492-1495		1
150	Enhancement of Optical Anisotropy by Interconnection Effect along Growth Direction in Multistacked Quantum Dots. *Japanese Journal of Applied Physics*, **2013**, 52, 012001	1.4	
149	Evaluation of minority and majority spin band energies of ferromagnetic GdN thin film using optical absorption spectroscopy **2013**,		1
148	One-dimensional miniband formation in closely stacked InAs/GaAs quantum dots. *Physical Review B* , **2013**, 87,	3.3	40
147	Giant optical splitting in the spin-states assisting a sharp magnetic switching in GdN thin films. *Applied Physics Letters*, **2013**, 102, 222408	3.4	8
146	Control of stacking direction and optical anisotropy in InAs/GaAs quantum dots by In flux. *Journal of Applied Physics*, **2013**, 114, 033517	2.5	5
145	Effects of pumping on propagation velocities of confined exciton polaritons in GaAs/AlxGa1−xAs double heterostructure thin films under resonant and non-resonant probe conditions. *Journal of Applied Physics*, **2013**, 113, 013514	2.5	1
144	Intraband carrier dynamics in InAs/GaAs quantum dots stimulated by bound-to-continuum excitation. *Journal of Applied Physics*, **2013**, 113, 223511	2.5	22
143	Magneto-optical effect in GdN epitaxial thin film. *Journal of Physics: Conference Series*, **2013**, 417, 012053	0.3	3
142	Correlation between local atomic structure and ultraviolet luminescence of AlGdN thin films. *Journal of Physics: Conference Series*, **2013**, 417, 012049	0.3	2
141	Atomically Controlled Growth of Self-Assembled Quantum Dots and Realization of Highly Functional Optical Responses. *Journal of Smart Processing*, **2013**, 2, 206-212	0.2	
140	High-resolution optical coherence tomography using broadband light source with strain-controlled InAs/GaAs quantum dots. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2012**, 9, 2473-2476		1
139	Effect of spacer layer thickness on multi-stacked InGaAs quantum dots grown on GaAs (311)B substrate for application to intermediate band solar cells. *Journal of Applied Physics*, **2012**, 111, 074305	2.5	18
138	Carrier dynamics of the intermediate state in InAs/GaAs quantum dots coupled in a photonic cavity under two-photon excitation. *Physical Review B*, **2012**, 86,	3.3	29
137	Near-field photoluminescence spectroscopy of CdTe/Cd0.75Mn0.25Te tilted superlattices. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2012**, 9, 262-265		
136	Study on spin-splitting phenomena in the band structure of GdN. *Applied Physics Letters*, **2012**, 100, 232410	3.4	18
135	Ferromagnetic properties of GdN thin films studied by temperature dependent circular polarized spectroscopy. *Applied Physics Letters*, **2012**, 101, 072403	3.4	11

134	Multiple excitation process in deep-ultraviolet emission from AlGdN thin films pumped by an electron beam. *Journal of Applied Physics*, **2012**, 111, 083526	2.5	3
133	Observation of quantum beat oscillations and ultrafast relaxation of excitons confined in GaAs thin films by controlling probe laser pulses. *Journal of Applied Physics*, **2012**, 111, 023505	2.5	10
132	Transient photoconductivity responses in amorphous In-Ga-Zn-O films. *Journal of Applied Physics*, **2012**, 112, 053715	2.5	35
131	Quantum Dot Switches: Towards Nanoscale Power-Efficient All-Optical Signal Processing **2012**, 197-221		
130	Increase in photocurrent by optical transitions via intermediate quantum states in direct-doped InAs/GaNAs strain-compensated quantum dot solar cell. *Journal of Applied Physics*, **2011**, 109, 024301	2.5	174
129	Suppression of nonradiative recombination process in directly Si-doped InAs/GaAs quantum dots. *Journal of Applied Physics*, **2011**, 110, 103511	2.5	21
128	Extremely uniform bound exciton states in nitrogen-doped GaAs studied by photoluminescence spectroscopy in external magnetic fields. *Journal of Applied Physics*, **2011**, 110, 083522	2.5	9
127	Ferromagnetic State of GdN Thin Film Studied by Ferromagnetic Resonance **2011**,		1
126	Saturation of Förster resonance energy transfer between two optically nonlinear cyanine dyes of small Stokes shift energies in polymer thin films. *Journal of Applied Physics*, **2011**, 110, 083521	2.5	4
125	Intermediate band photovoltaics based on interband–intraband transitions using In0.53Ga0.47As/InP superlattice. *Progress in Photovoltaics: Research and Applications*, **2011**, 21, n/a-n/a	6.8	7
124	Bound biexciton luminescence in nitrogen-doped GaAs. *Physica Status Solidi (B): Basic Research*, **2011**, 248, 464-467	1.3	7
123	Propagation velocity of excitonic polaritons confined in GaAs thin films. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2011**, 8, 378-380		3
122	Energy band structure and the half-filling of the intermediate band in the quantum-dot solar cell. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2011**, 8, 622-624		3
121	Interaction between conduction-band edge and nitrogen-related localized levels in nitrogen -doped GaAs. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2011**, 8, 365-367		1
120	Broadband light sources using InAs quantum dots with InGaAs strain-reducing layers. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2011**, 8, 331-333		14
119	Optical and ferromagnetic properties of GdN thin films. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2011**, 8, 488-490		6
118	Intraband relaxation process in highly stacked quantum dots. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2011**, 8, 46-49		3
117	Excitation power dependence of nonlinear optical response of excitons in GaAs/AlAs superlattices. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2011**, 8, 50-53		2

116	Optical and magnetic properties in epitaxial GdN thin films. *Physical Review B*, **2011**, 83,	3.3	41
115	Depolarization effect on optical control of exciton states confined in GaAs thin films. *Journal of Applied Physics*, **2011**, 110, 043514	2.5	2
114	Experimental and atomistic theoretical study of degree of polarization from multilayer InAs/GaAs quantum dot stacks. *Physical Review B*, **2011**, 84,	3.3	41
113	Dynamics of above-barrier state excitons in multi-stacked quantum dots. *Journal of Applied Physics*, **2011**, 110, 093515	2.5	2
112	Observation of phase shifts in a vertical cavity quantum dot switch. *Applied Physics Letters*, **2011**, 98, 231101	3.4	18
111	Influence of local atomic configuration in AlGdN phosphor thin films on deep ultra-violet luminescence intensity. *Journal of Applied Physics*, **2011**, 110, 093108	2.5	7
110	Field-emission properties of carbon nanotube composite in side-electron emission configuration. *Journal of Applied Physics*, **2011**, 109, 074307	2.5	5
109	Ultraviolet Light Emitting Devices Using AlGdN. *Materials Research Society Symposia Proceedings*, **2011**, 1342, 55		
108	Multidirectional Observation of Photoluminescence Polarization Anisotropy in Closely Stacked InAs/GaAs Quantum Dots. *Applied Physics Express*, **2011**, 4, 062001	2.4	36
107	Dephasing of Excitonic Polaritons Confined in GaAs Thin Films. *Journal of the Physical Society of Japan*, **2011**, 80, 034704	1.5	3
106	Highly Efficient Ultra-Violet Luminescence from Low-Temperature Grown AlGdN. *Zairyo/Journal of the Society of Materials Science, Japan*, **2010**, 59, 666-670	0.1	
105	Temperature dependence of photoluminescence characteristics of excitons in stacked quantum dots and quantum dot chains. *Journal of Applied Physics*, **2010**, 107, 073506	2.5	11
104	Effects of absorption coefficients and intermediate-band filling in InAs/GaAs quantum dot solar cells. *Applied Physics Letters*, **2010**, 97, 193106	3.4	34
103	Statistical fluctuation of magnetization in Mn-composition modulated Cd1−MnxTe quantum wires. *Journal of Applied Physics*, **2010**, 107, 043521	2.5	1
102	All-optical switch using InAs quantum dots in a vertical cavity **2010**,		1
101	Polarization control of electroluminescence from vertically stacked InAs/GaAs quantum dots. *Applied Physics Letters*, **2010**, 96, 211906	3.4	31
100	Impurity doping in self-assembled InAs/GaAs quantum dots by selection of growth steps. *Journal of Applied Physics*, **2010**, 108, 063524	2.5	25
99	Temperature-dependent carrier tunneling for self-assembled InAs/GaAs quantum dots with a GaAsN quantum well injector. *Applied Physics Letters*, **2010**, 96, 151104	3.4	22

98	Multi-stacked InAs/GaNAs quantum dots with direct Si doping for use in intermediate band solar cell **2010**,		4
97	Vertically stacked InAs quantum dots for polarization-independent semiconductor optical amplifiers **2010**,		6
96	Energy band structure and absorption coefficients in the quantum-dot intermediate band solar cells **2010**,		1
95	Vertical stacking of InAs quantum dots for polarization-insensitive semiconductor optical amplifiers. *Journal of Physics: Conference Series*, **2010**, 245, 012076	0.3	4
94	Spatially Resolved Thermal Conductivity of Intermetallic Compounds Measured by Micro-Thermoreflectance Method. *Nippon Kinzoku Gakkaishi/Journal of the Japan Institute of Metals* , **2010**, 74, 740-745	0.4	2
93	Detailed Design and Characterization of All-Optical Switches Based on InAs/GaAs Quantum Dots in a Vertical Cavity. *IEEE Journal of Quantum Electronics*, **2010**, 46, 1582-1589	2	14
92	Exciton response controlled by introducing a spacer layer in nitrided InAs quantum dots. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2009**, 6, S146-S149		1
91	Transient reflectivity response with negative time delay caused by femtosecond pulse propagation in GaAs thin films. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2009**, 6, S139-S142		3
90	Side electron emission device using a composite of carbon nanofibers and aluminum. *Thin Solid Films*, **2009**, 518, 530-533	2.2	3
89	Anisotropic linear-polarization luminescence in CdTe/CdMnTe quantum wires. *Journal of Luminescence*, **2009**, 129, 1448-1453	3.8	
88	Vertical-geometry all-optical switches based on InAs/GaAs quantum dots in a cavity. *Applied Physics Letters*, **2009**, 95, 021109	3.4	31
87	Analysis of thermoreflectance signals and characterization of thermal conductivity of metal thin films. *Review of Scientific Instruments*, **2009**, 80, 124901	1.7	11
86	Thermal Conductivity Measurement Technique for Cu-Pt Alloy Thin Films by a Modulated Thermoreflectance Method. *Nippon Kinzoku Gakkaishi/Journal of the Japan Institute of Metals*, **2009** , 73, 434-438	0.4	6
85	Narrowband ultraviolet field-emission device using Gd-doped AlN. *IOP Conference Series: Materials Science and Engineering*, **2009**, 1, 012001	0.4	10
84	Anisotropic magneto-optical effects in CdTe/Cd0.75Mn0.25Te quantum wire structures. *Physical Review B*, **2008**, 78,	3.3	3
83	Real time analysis of self-assembled InAs/GaAs quantum dot growth by probing reflection high-energy electron diffraction chevron image. *Journal of Applied Physics*, **2008**, 104, 074305	2.5	17
82	Effects of indium segregation on optical properties of nitrogen-doped InAs/GaAs quantum dots. *Journal of Applied Physics*, **2008**, 104, 103532	2.5	4
81	Photoluminescence characteristics of quantum dots with electronic states interconnected along growth direction. *Journal of Applied Physics*, **2008**, 103, 113504	2.5	38

80	Fine structure splitting of isoelectronic bound excitons in nitrogen-doped GaAs. *Physical Review B*, **2008**, 77,	3.3	20
79	Side electron emission device using carbon nanofiber/elastomer composite sheet. *Applied Physics Letters*, **2008**, 92, 243302	3.4	12
78	Electron tomography of embedded semiconductor quantum dot. *Applied Physics Letters*, **2008**, 92, 031902	3.4	35
77	Dual chopped photoreflectance spectroscopy for nondestructive characterization of semiconductors and semiconductor nanostructures. *Review of Scientific Instruments*, **2008**, 79, 046110	1.7	11
76	Narrow-band deep-ultraviolet light emitting device using Al1−xGdxN. *Applied Physics Letters*, **2008**, 93, 211901	3.4	14
75	Ultrafast All-Optical Control of Excitons Confined in GaAs Thin Films. *Applied Physics Express*, **2008**, 1, 112401	2.4	4
74	Flexible Field Emission Device Using Carbon Nanofiber Nanocomposite Sheet. *Applied Physics Express*, **2008**, 1, 074004	2.4	6
73	Photoluminescence dynamics of coupled quantum dots. *Journal of Luminescence*, **2008**, 128, 975-977	3.8	5
72	Emission-wavelength extension of nitrided InAs/GaAs quantum dots with different sizes. *Journal of Crystal Growth*, **2007**, 301-302, 709-712	1.6	3
71	Atomically controlled doping of nitrogen on GaAs(0 0 1) surfaces. *Journal of Crystal Growth*, **2007**, 301-302, 34-37	1.6	7
70	Bright electron emission from Si-doped AlN thin films. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2007**, 4, 2490-2493		9
69	Multidirectional observation of an embedded quantum dot. *Applied Physics Letters*, **2007**, 90, 041911	3.4	9
68	High-Brightness Electron Emission from Flexible Carbon Nanotube/Elastomer Nanocomposite Sheets. *Japanese Journal of Applied Physics*, **2006**, 45, L1186-L1189	1.4	20
67	Carbon Nanotube/Aluminum Composites As a Novel Field Electron Emitter. *Japanese Journal of Applied Physics*, **2006**, 45, L650-L653	1.4	16
66	Anisotropic magneto-optical effects in one-dimensional diluted magnetic semiconductors. *Physical Review B*, **2006**, 74,	3.3	16
65	Bound exciton states of isoelectronic centers in GaAs:N grown by an atomically controlled doping technique. *Physical Review B*, **2006**, 74,	3.3	34
64	Artificial control of optical gain polarization by stacking quantum dot layers. *Applied Physics Letters*, **2006**, 88, 211106	3.4	68
63	Valence-band mixing induced by sp-d exchange interaction in CdMnTe quantum wires. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2006**, 3, 667-670		1

62	Anisotropic exchange interaction caused by hole-spin reorientation in (CdTe)0.5(Cd0.75Mn0.25Te)0.5 tilted superlattices grown on Cd0.74Mg0.26Te(001) vicinal surface. *Journal of Crystal Growth*, **2005**, 275, e2221-e2224	1.6	3
61	Optical Polarization Properties of InAs/GaAs Quantum Dot Semiconductor Optical Amplifier. *Japanese Journal of Applied Physics*, **2005**, 44, 2528-2530	1.4	5
60	Ultrafast Anisotropic Processes of Exciton Magnetic Polarons in CdTe/CdMnTe Quantum Wires. *Springer Series in Chemical Physics*, **2005**, 263-265	0.3	
59	Extended wavelength emission to 1.3□m in nitrided InAs□GaAs self-assembled quantum dots. *Journal of Applied Physics*, **2005**, 97, 024306	2.5	10
58	Anisotropic magneto-optical effects in (CdTe)0.5(Cd0.75Mn0.25Te)0.5 tilted superlattices. *Physical Review B*, **2004**, 69,	3.3	9
57	Anisotropic exchange interaction in CdTe/Cd0.75Mn0.25Te quantum wires. *Physica E: Low-Dimensional Systems and Nanostructures*, **2004**, 21, 345-348	3	1
56	Control of optical polarization anisotropy in edge emitting luminescence of InAs/GaAs self-assembled quantum dots. *Applied Physics Letters*, **2004**, 84, 1820-1822	3.4	48
55	Temperature Dependence of GaAs1-xBixBand Gap Studied by Photoreflectance Spectroscopy. *Japanese Journal of Applied Physics*, **2003**, 42, 371-374	1.4	164
54	Strain effects on photoluminescence polarization of InAs/GaAs self-assembled quantum dots. *Physica Status Solidi (B): Basic Research*, **2003**, 238, 229-232	1.3	3
53	Polarization controlled edge emission from columnar InAs/GaAs self-assembled quantum dots. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2003**, 1137-1140		8
52	Fourier transformed photoreflectance characterization of interface electric fields in GaAs/GaInP heterojunction bipolar transistor wafers. *Journal of Applied Physics*, **2003**, 94, 6487-6490	2.5	5
51	Transition with a hysteresis cycle in surface reconstruction on GaAs(001) observed by optical reflectance spectroscopy. *Physical Review B*, **2003**, 67,	3.3	5
50	Excitonic states in CdTe/Cd0.74Mg0.26Te quantum wires grown on vicinal substrates. *Physical Review B*, **2003**, 67,	3.3	2
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